/ Descriptions

TO-252

Ultrafast Recovery Diode in a TO-252 Plastic Package.

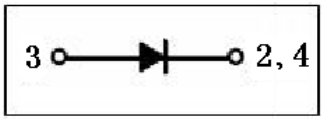
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

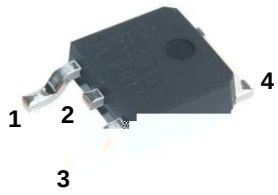
/ Applications

For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.

/ Equivalent Circuit



/ Pinning



PIN1 NC PIN 2 Cathode PIN 3 Anode PIN 4:Case

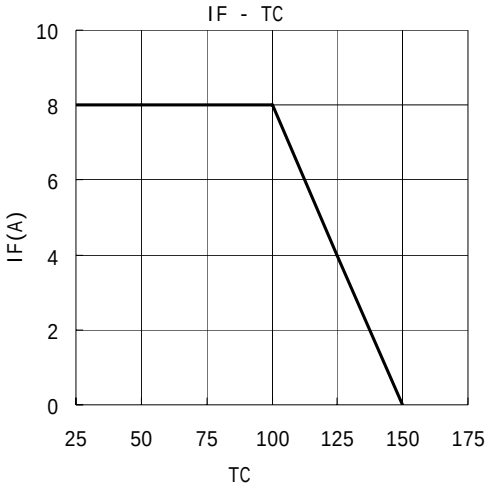
/ h_{FE} Classifications & Marking

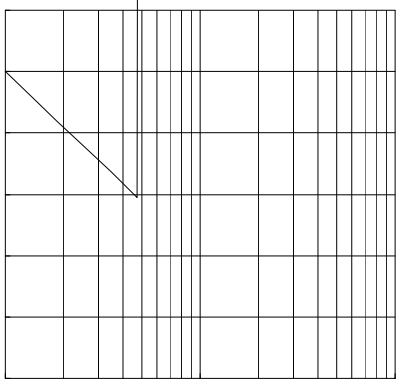
See Marking Instructions.

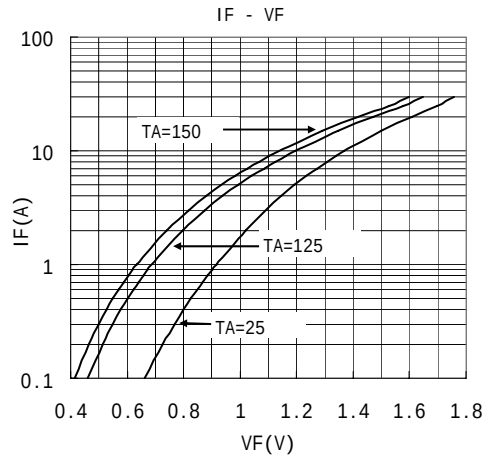
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
Working Peak Reverse Voltage	V_{RMS}	420	V
Average Rectified Forward Current	I_F	8	A
Non Repetitive Peak Surge Current	I_{FSM}	125	A
Thermal resistance, junction to case	$R_{\theta Jc}$	3.5	/W
Junction and Storage Temperature Range	T_j T_{stg}	-55 150	

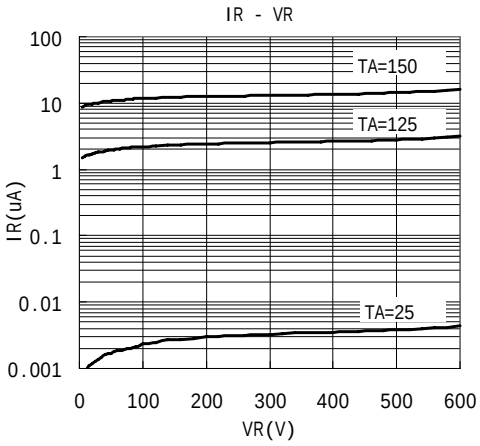
Forward Voltage	V_F	I_F=8A	Tc=25		1.4	1.7	V
		I_F=16A	Tc=25		1.7	2.1	V
		I_F					

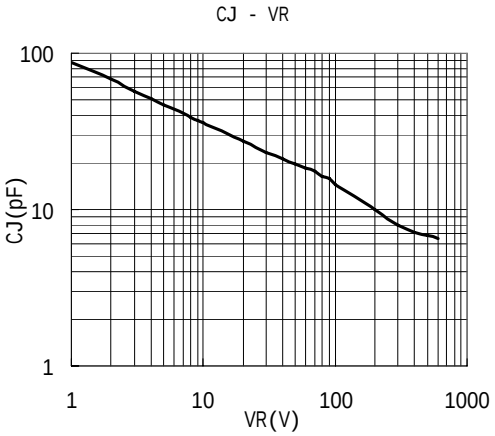
/ Electrical Characteristic Curve



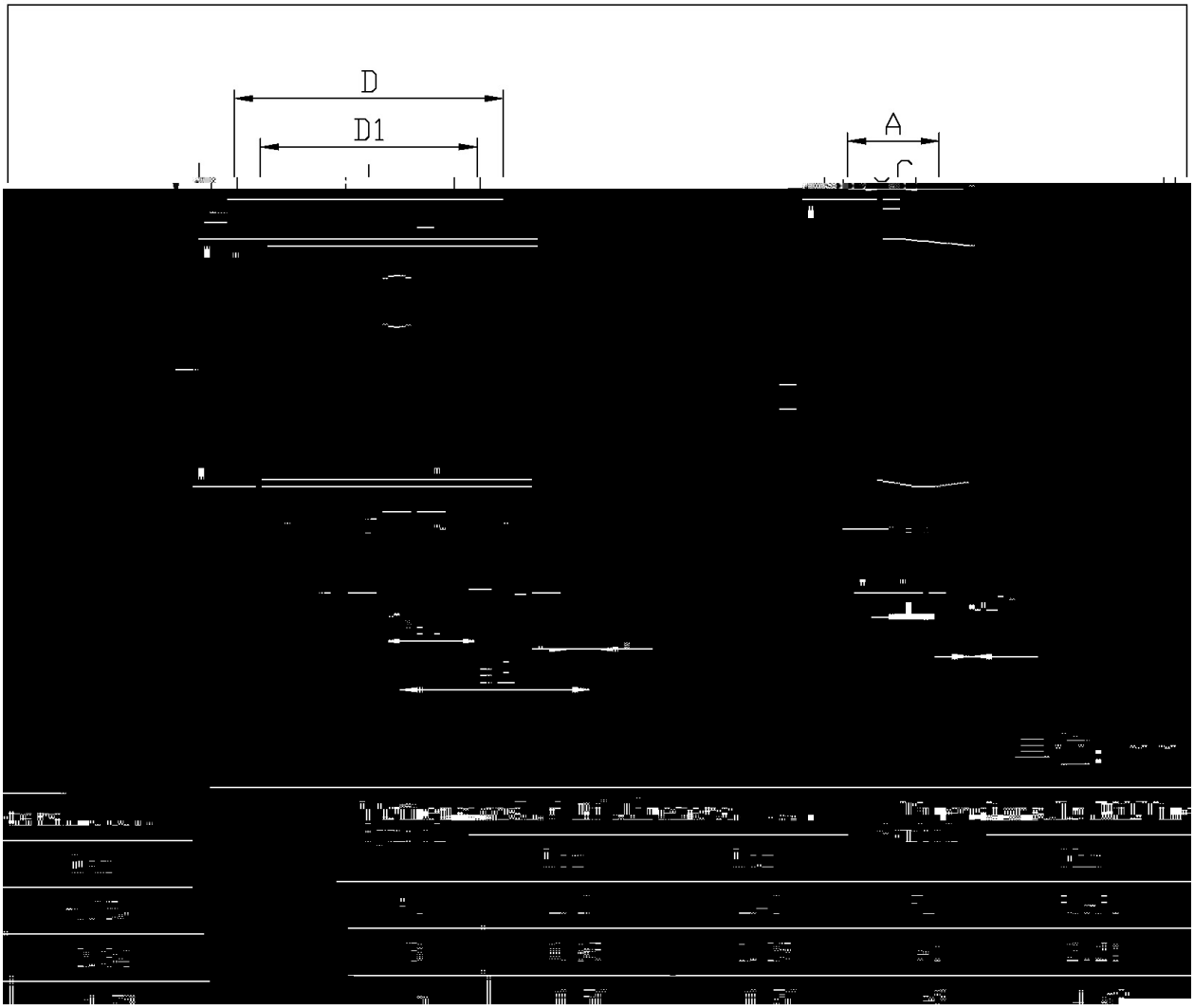








/ Package Dimensions



/ Marking Instructions



BR

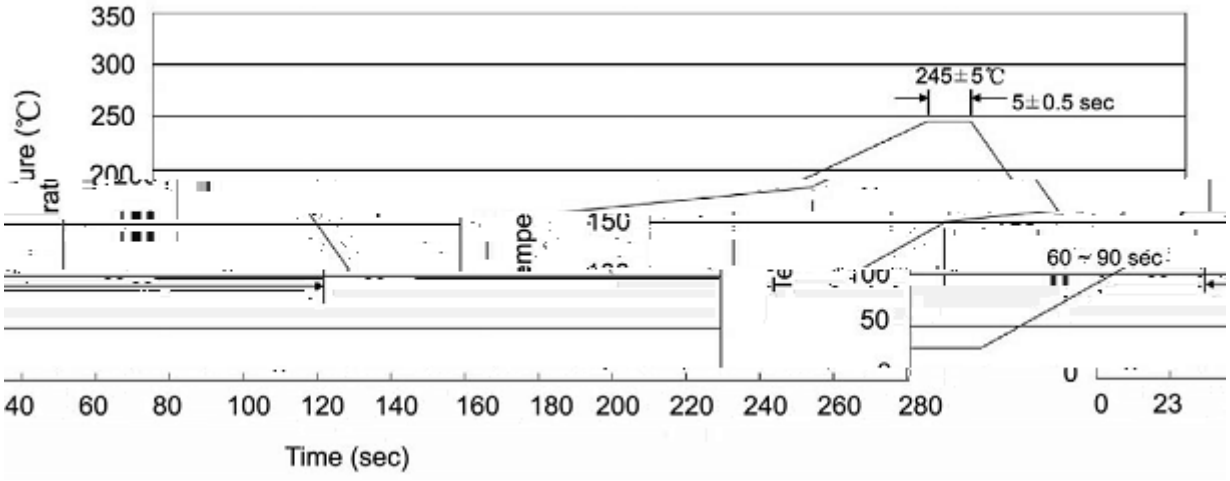
MUR860

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Note:

BR:	Company Code
MUR860	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



1		25	150		60	90sec;	Note: 1.Preheating:25~150 , Time:60~90sec.
2		245±5				5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3				2	10	/sec.	3. Cooling Speed: 2~10 /sec.

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